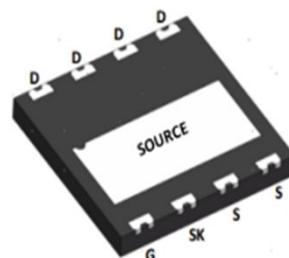


Description

Product Summary		
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ)	I _D (A)
700	125	12.6



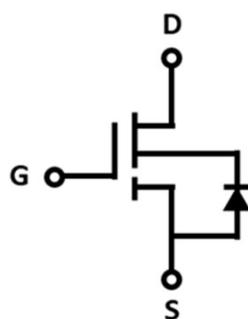
Feature

- Easy to use, compatible with standard gate drivers
- Excellent Q_G x R_{DS(on)} figure of merit (FOM)
- Low Q_{RR}, no free-wheeling diode required
- Low switching loss
- RoHS compliant and Halogen-free

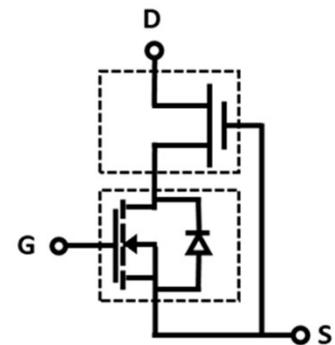
Applications

- High efficiency power supplies
- Telecom and datacom
- Automotive
- Servo motors

DFN8080-8L (Bottom View)



Schematic Symbol



**Cascode
Device Structure**

Absolute maximum rating@25°C

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	700	V
Gate-Source Voltage	V _{GS}	±20	V
Transient Drain-Source Voltage ¹⁾	V _{TDS}	800	V
Continuous Drain Current	T _C =25°C	I _D	A
	T _C =100°C		
Pulsed Drain Current (Pulse Width: 100μs)	T _C =25°C	I _{DM}	A
	T _C =125°C		
Power Dissipation	P _D	38	W
Soldering Peak Temperature	T _{CSOLD}	260	°C
Operating Junction and Storage Temperature	T _J , T _{STG}	-55 to 150	°C

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	R _{θJC}	-	3.3	-	°C/W
Thermal Resistance, Junction-to-Ambient ²⁾	R _{θJA}	-	50	-	°C/W

700V GaN Power Transistor

PGC8FN700R125B

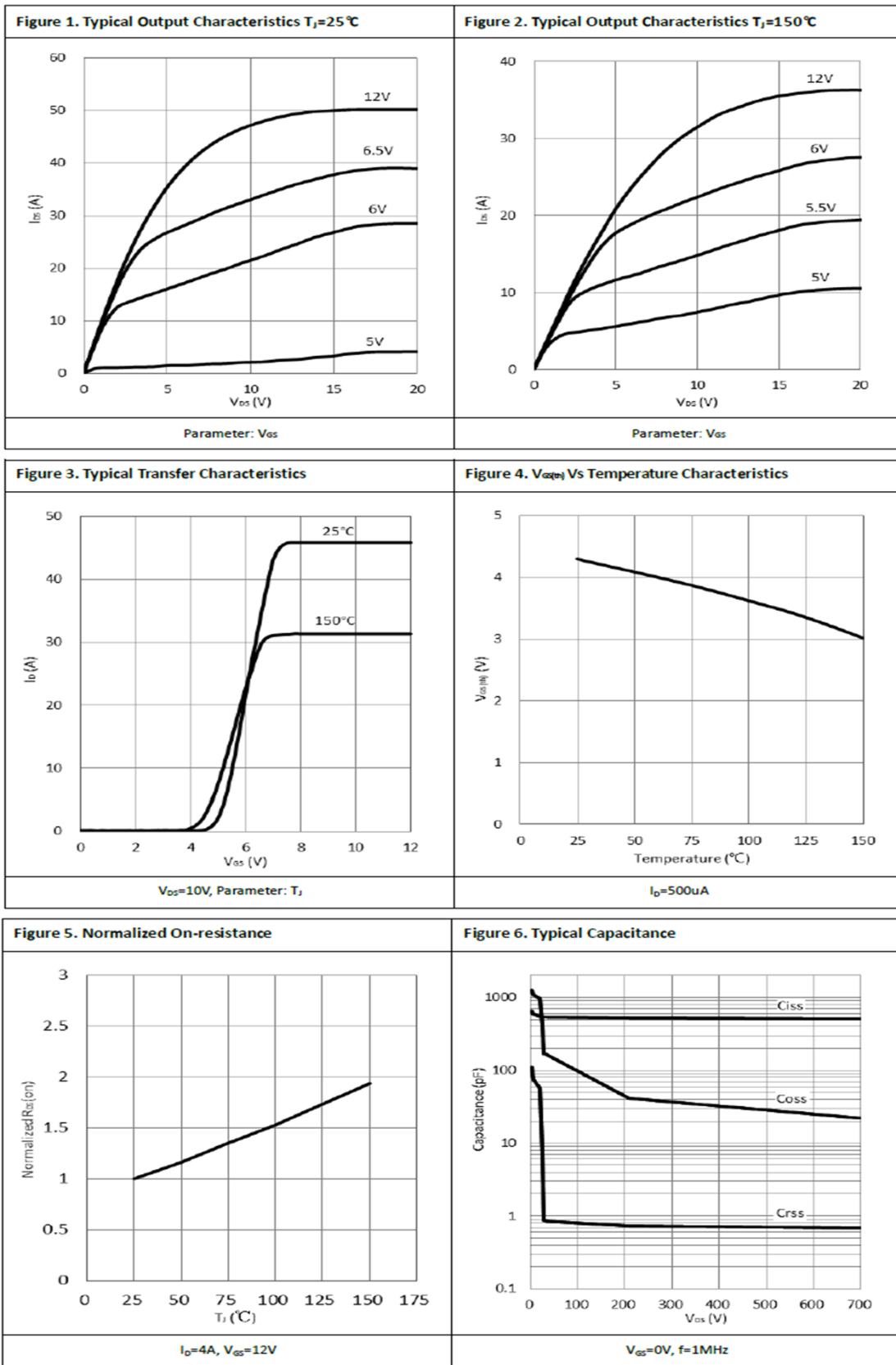
Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Units	
Statistic Characteristics								
Maximum Drain-Source Voltage	V _{DS-Max}	V _{GS} = 0V		700	-	-	V	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA		-	1000	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =700V, V _{GS} =0V	T _J =25°C	-	10	20	μA	
			T _J =150°C	-	50	-		
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V		-	-	±150	nA	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 500μA	3.0	4.0	5.0	-	V	
Gate Threshold Voltage Temperature Coefficient	△V _{GS(th)} /T _J			-	-10.7	-	mV/°C	
Drain-Source On-State Resistance ³⁾	R _{DS(ON)}	V _{GS} =12V, I _D =4A	T _J =25°C	-	125	160	mΩ	
			T _J =150°C	-	250	-		
Dynamic Characteristics								
Input Capacitance	C _{iss}	V _{DS} = 400V, V _{GS} = 0V, f = 1MHz	V _{DS} = 400V, V _{GS} = 0V, f = 1MHz	-	506	-	pF	
Output Capacitance	C _{oss}			-	28	-		
Reverse Transfer Capacitance	C _{rss}			-	0.7	-		
Effective Output Capacitance, Energy Related	C _{o(er)}	V _{GS} = 0V, V _{DS} = 0-400V	V _{GS} = 0V, V _{DS} = 0-400V	-	46	-	pF	
Effective Output Capacitance, Time Related	C _{o(tr)}			-	108	-		
Output Charge	Q _{oss}			-	43	-	nC	
Turn-on Delay Time	t _{d(on)}	V _{DS} = 400V, I _D = 8A, V _{GS} = 0-12V, R _G = 40Ω	V _{DS} = 400V, I _D = 8A, V _{GS} = 0-12V, R _G = 40Ω	-	44	-	ns	
Turn-on Rise Time	t _r			-	16	-		
Turn-Off Delay Time	t _{d(off)}			-	40	-		
Turn-Off Fall Time	t _f			-	12	-		
Total Gate Charge	Q _g	V _{DS} = 400V, I _D = 8A, V _{GS} = 0-12V	V _{DS} = 400V, I _D = 8A, V _{GS} = 0-12V	-	16	-	nC	
Gate-Source Charge	Q _{gs}			-	4.8	-		
Gate-Drain Charge	Q _{gd}			-	4.4	-		
Reverse Diode Characteristics								
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =4A		-	1.2	-	V	
		V _{GS} =0V, I _S =8A	T _J =25°C	-	1.6	-		
			T _J =150°C	-	2.2	-		
Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _S =8A, V _{DD} =400V, di/dt=1000A/μs		-	21	-	ns	
Reverse Recovery Charge	Q _{rr}			-	43	-	μC	

Notes:

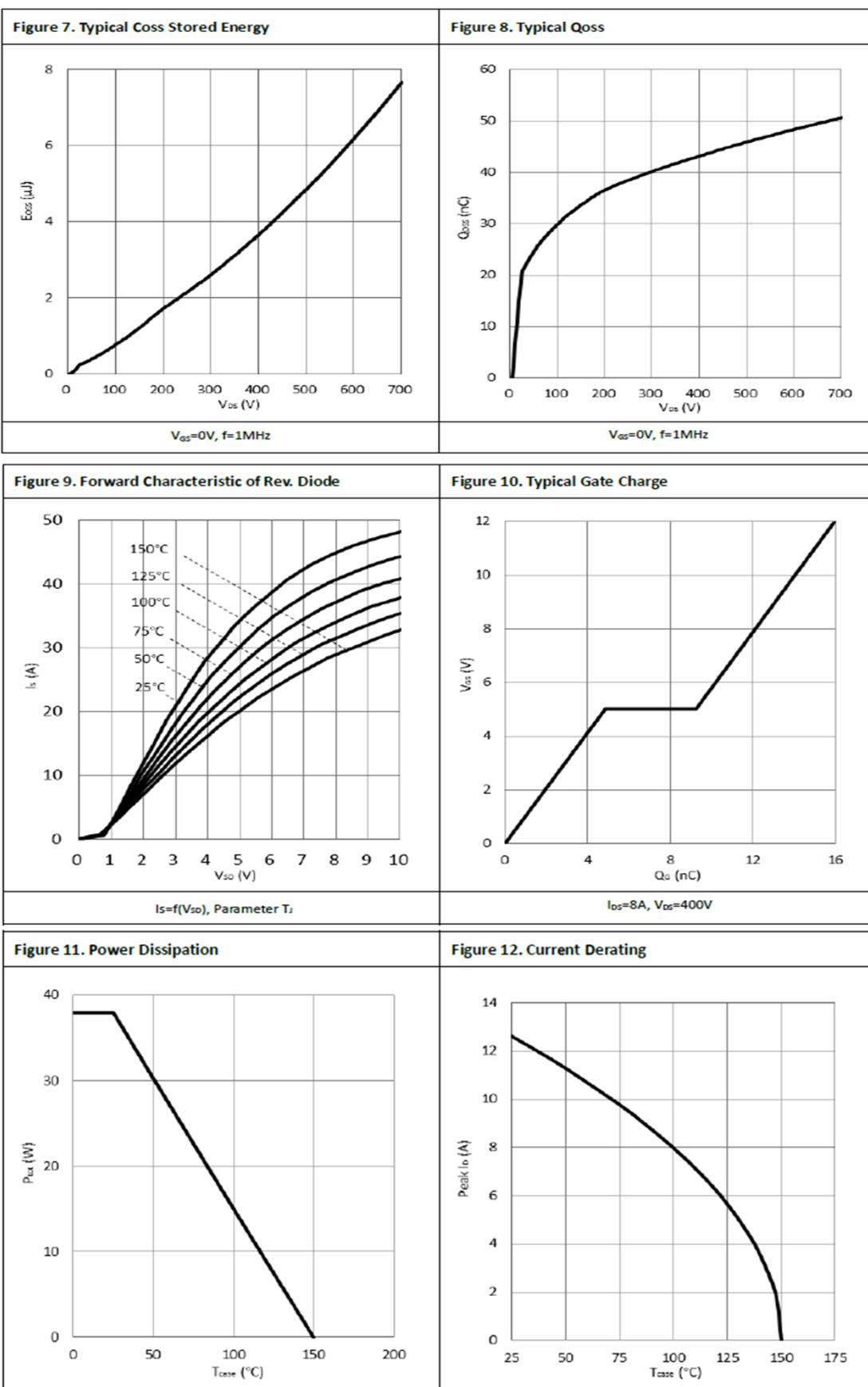
1. Off-state spike duty cycle < 0.01, spike duration < 2μs
2. Device on one layer epoxy PCB for drain connection (vertical and without air stream cooling, with 6cm²copper area and 70μm thickness)
3. Dynamic on-resistance; see Figure 18 and 19 for test circuit and configurations

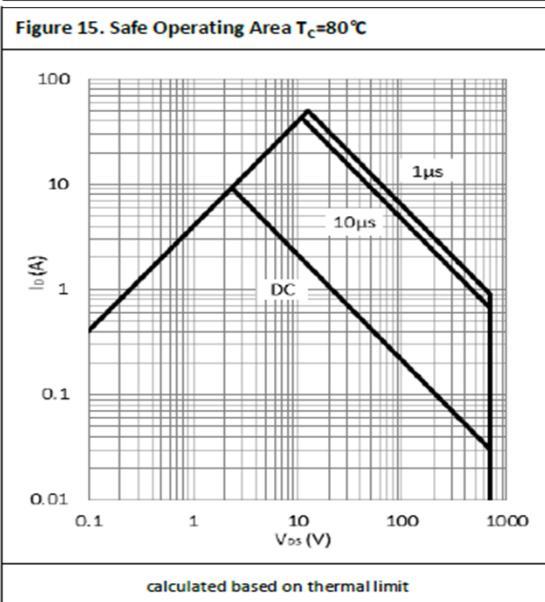
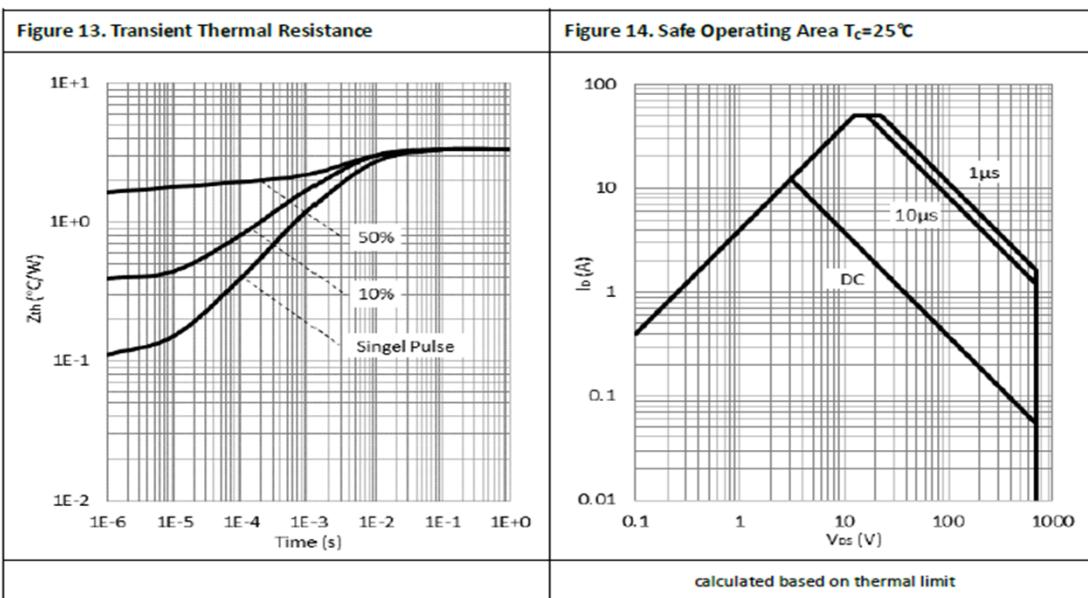
Typical Characteristics



700V GaN Power Transistor

PGC8FN700R125B





Test Circuits and Waveforms

Figure 16. Switching Time Test Circuit

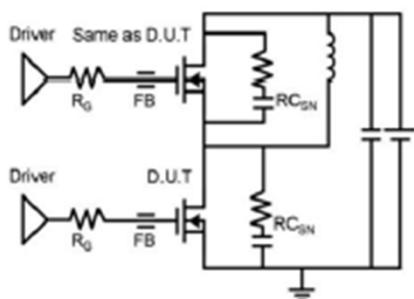


Figure 17. Switching Time Waveform

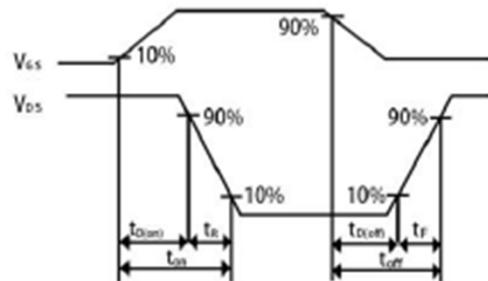


Figure 18. Dynamic RDS(on) Test Circuit

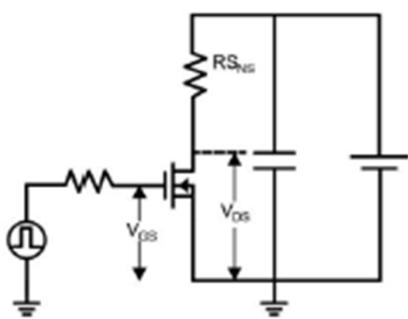


Figure 19. Dynamic RDS(on) Waveform

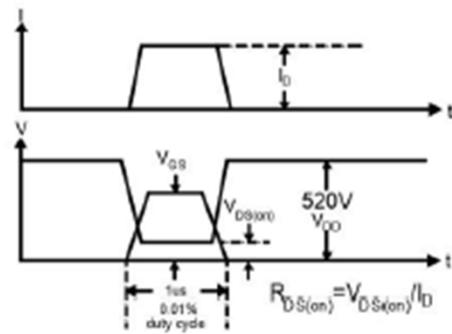


Figure 20. Diode Characteristic Test Circuits

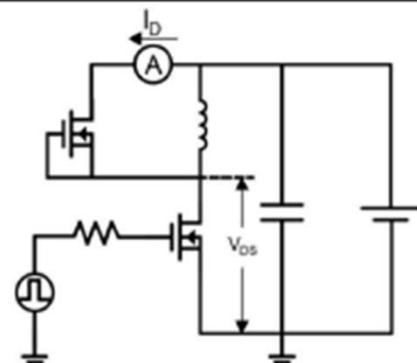
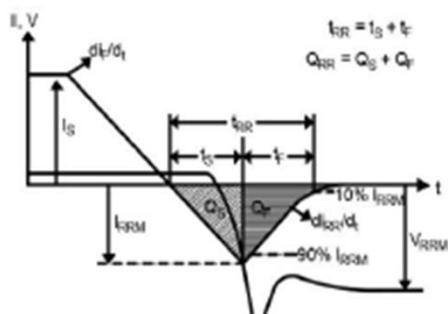
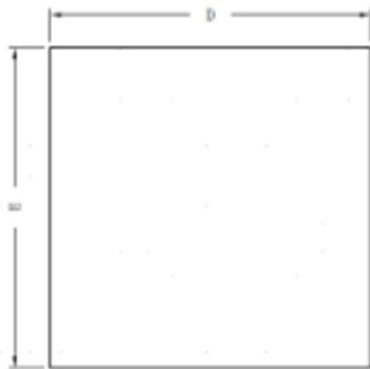


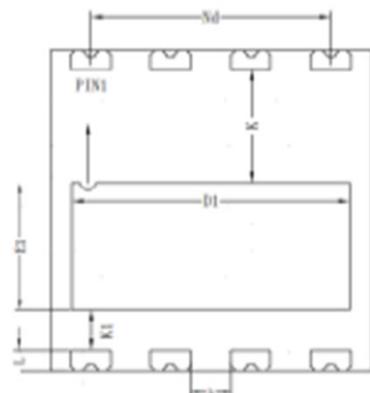
Figure 21. Diode Recovery Waveform



Product Dimension (DFN8080-8L)



TOP VIEW



BOTTOM VIEW



SIDE VIEW

SYMBOL	Millimeter		
	Min	Nom	Max
A	0.80	0.90	1.15
A1	0	0.02	0.05
c	—	0.20	—
b	0.90	1.00	1.10
D	7.90	8.00	8.10
D1	6.85	6.95	7.05
E	7.90	8.00	8.10
E1	3.10	3.20	3.30
e	2.00BSC		
Nd	6.00BSC		
K	2.70	2.80	2.90
K1	0.90	1.00	1.10
L	0.40	0.50	0.60

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